

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (previously presented): A method for forming integrated circuit copper lines, comprising:

forming a trench in a dielectric layer;

forming a first metal layer in said trench using physical vapor deposition and a high atomic number metal wherein said high atomic number metal is selected from a group consisting of Ruthenium, Iridium, and Rhodium;

forming a second metal layer in said trench contacting on said first metal layer using chemical vapor deposition and a high atomic number metal wherein said high atomic number metal is selected from a group consisting of Ruthenium, Iridium, and Rhodium; and

filling said trench with copper by electroplating copper directly on said second metal layer.

Claim 2 (canceled)

Claim 3 (original): The method of claim 1 wherein said forming a first metal layer in said trench comprises forming a Ruthenium layer using a plasma excitation power of 100 to 1000 watts with a DC power of 5KW to 30 KW applied to a sputter metal target.

Claim 4 (original): The method of claim 1 wherein said forming a second metal layer in said trench comprises flowing a vapor containing Ruthenium over a surface heated to between 100°C and 350°C.

Claim 5 (previously presented): The method of claim 1 further comprising forming a third metal layer in said trench contacting on said second metal layer using chemical vapor deposition and a metal selected from a group consisting of Ruthenium, Iridium, and Rhodium.

Claim 6 (previously presented): The method of claim 5 further comprising forming a fourth metal layer in said trench contacting said third metal layer using chemical vapor deposition and a high atomic number metal.

Claim 7 (currently canceled)

Claim 8 (currently canceled)

Claim 9 (currently canceled)

Claim 10 (currently canceled)

Claims 11-16 (canceled)

Claims 17-22 (currently canceled)